

MMC, SD CARD, Memory Stick[™] VOLTAGE-TRANSLATION TRANSCEIVER WITH ESD PROTECTION AND EMI FILTERING

Check for Samples: TXS0206

FEATURES

- Level Translator
 - V_{CCA} and V_{CCB} Range of 1.1 V to 3.6 V
 - Fast Propagation Delay (4 ns Max When Translating Between 1.8 V and 3 V)
- Integrated EMI Filtering and ESD Protection Circuitry
- ESD Protection Exceeds JESD 22 (A Port)
 - 2500-V Human-Body Model (A114-B)
 - 250-V Machine Model (A115-A)
 - 1500-V Charged-Device Model (C101)
- ±8-kV Contact Discharge IEC 61000-4-2 ESD (B-port)

	YFP (T	PA OP	VIE	(AG EW)	E
	1	2	3	4	_
A	\bigcirc	\bigcirc	\bigcirc	()	
В	\bigcirc	()	()	\bigcirc	
С	\bigcirc	()	()	\bigcirc	
D	\bigcirc	()	()	()	
E	()	\bigcirc	\bigcirc	()	

TERMINAL ASSIGNMENTS

	1	2	3	4
Α	DAT2A	V _{CCA}	WP	DAT2B
в	DAT3A	CD	V _{CCB}	DAT3B
С	CMDA	GND	GND	CMDB
D	DAT0A	CLKA	CLKB	DAT0B
Е	DAT1A	CLK-f	EN	DAT1B

DESCRIPTION/ORDERING INFORMATION

The TXS0206 is a level shifter for interfacing microprocessors with MultiMediaCards (MMCs), secure digital (SD) cards, and Memory Stick[™] cards. It includes a high-speed level translator along with ESD protection and EMI filtering circuitry.

The voltage-level translator has two supply voltage pins. V_{CCA} as well as V_{CCB} can be operated over the full range of 1.1 V to 3.6 V. The TXS0206 enables system designers to easily interface applications processors or digital basebands to memory cards and SDIO peripherals operating at a different I/O voltage level.

Memory card standards recommend high-ESD protection for devices that connect directly to the external memory card. To meet this need, the TXS0206 incorporates ±8-kV Contact Discharge protection on the card side.

The TXS0206 is offered in a 20-bump wafer chip scale package (WCSP). This package has dimensions of 1.96 mm x 1.56 mm, with a 0.4-mm ball pitch for effective board-space savings. Memory cards are widely used in mobile phones, PDAs, digital cameras, personal media players, camcorders, set-top boxes, etc. Low static power consumption and small package size make the TXS0206 an ideal choice for these applications.

ORDERING INFORMATION⁽¹⁾

T _A	PACKAGE ⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽³⁾
-40°C to 85°C	WCSP – YFP (Pb-free)	Tape and reel	TXS0206YFPR	3T_

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

YFP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following (3)character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, •= Pb-free).



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Figure 1. Interfacing With SD/SDIO Card





NOTE: The TXS0206 has integrated pullup resistor values that dynamically change value depending on whether a low or high signal is being transmitted through the device. When the output is low, the TXS0206 internal pullup value is 40 kΩ, and when the output is high, the internal pullup value change to a value of 4 kΩ. For MSA and MSH Memory Stick[™] memory cards, to ensure that a valid V_{IH} (i.e., receiver input voltage high) is achieved, the internal pulldown resistors for these memory cards are not smaller than a 10-kΩ value. See the *Application Information* section of this data sheet, which explains the impact of adding too heavy (i.e., <10-kΩ value) of a pulldown resistor to the data lines of the TXS0206 device and the resulting 4-kΩ pullup/10-kΩ pulldown voltage divider network, which has a direct impact on the V_{IH} of the signal being sent into the Memory Stick[™].

Figure 2. Interfacing With Memory Stick[™] Card



Integrated Pullup/Pulldown Resistors

Figure 3. Typical Application Circuit

EN	TRANSLATOR I/Os					
L	Disabled, pulled to V_{CCA},V_{CCB} through 40 $k\Omega$					
Н	Active					

LOGIC TABLE

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INSTRUMENTS

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TERMINAL FUNCTIONS

TERMINAL		TYPE	DESCRIPTION			
NO.	NAME	TIPE	DESCRIPTION			
A1	DAT2A	I/O	Data bit 2 connected to host. Referenced to V_{CCA} . Includes a 40-k Ω pullup resistor to V_{CCA} .			
A2	V _{CCA}	Pwr	A-port supply voltage. V _{CCA} powers all A-port I/Os and control inputs.			
A3	WP	0	Connected to write protect on the mechanical connector. The WP pin has an internal 100-k Ω pullup resistor to V _{CCA} .			
A4	DAT2B	I/O	Data bit 2 connected to memory card. Referenced to V_{CCB} . Includes a 40-k Ω pullup resistor to V_{CCB} .			
B1	DAT3A	I/O	Data bit 3 connected to host. Referenced to V_{CCA} . Includes a 40-k Ω pullup resistor to V_{CCA} .			
B2	CD	0	Connected to card detect on the mechanical connector. The CD pin has an internal 100-k Ω pullup resistor to $V_{CCA}.$			
B3	V _{CCB}	Pwr	B-port supply voltage. V _{CCB} powers all B-port I/Os.			
B4	DAT3B	I/O	Data bit 3 connected to memory card. Referenced to V_{CCB} . Includes a 40-k Ω pullup resistor to V_{CCB} .			
C1	CMDA	I/O	Command bit connected to host. Referenced to V_{CCA} . Includes a 40-k Ω pullup resistor to V_{CCA} .			
C2, C3	GND		Ground			
C4	CMDB	I/O	Command bit connected to memory card. Referenced to V_{CCB} . Includes a 40-k Ω pullup resistor to V_{CCB} .			
D1	DAT0A	I/O	Data bit 0 connected to host. Referenced to V_{CCA} . Includes a 40-k Ω pullup resistor to V_{CCA} .			
D2	CLKA	I	Clock signal connected to host. Referenced to V _{CCA} .			
D3	CLKB	0	Clock signal connected to memory card. Referenced to V _{CCB} .			
D4	DAT0B	I/O	Data bit 0 connected to memory card. Referenced to V_{CCB} . Includes a 40-k Ω pullup resistor to V_{CCB} .			
E1	DAT1A	I/O	Data bit 1 connected to host. Referenced to V_{CCA} . Includes a 40-k Ω pullup resistor to V_{CCA} .			
E2	CLK-f	0	Clock feedback to host for resynchronizing data to a processor. Leave unconnected if not used.			
E3	EN	Ι	Enable/disable control. Pull EN low to place all outputs in Hi-Z state. Referenced to V _{CCA} .			
E4	DAT1B	I/O	Data bit 1 connected to memory card. Referenced to V_{CCB} . Includes a 40-k Ω pullup resistor to V_{CCB} .			









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RESISTORS			BIDIRECTIONAL ZE	NER DIODES
R1, R2, R3, R4, R5, R6	40 Ω		Vbr min	14 V at 1 mA
Tolerance	±20%		Line capacitance	<20 pF
R7, R8, R9, R10, R11	40 kΩ			
Tolerance	±30%			

Figure 5. ASIP Block Diagram



RESI	STORS
R_{WP}, R_{CD}	100 kΩ
Tolerance	±30%

Figure 6. WP, CD Pullup Resistors



ABSOLUTE MAXIMUM RATINGS⁽¹⁾ Level Translator

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT	
V _{CCA}	Supply voltage range			4.6	V	
V _{CCB}	Supply voltage range	-0.5	4.6	V		
		I/O ports (A port)	-0.5	4.6		
VI	Input voltage range	I/O ports (B port)	-0.5	4.6	V	
		Control inputs	-0.5	4.6		
V	Voltage range applied to any output in the high-impedance or power-off	A port	-0.5	4.6	V	
vo	state	B port	-0.5	4.6		
v	Voltage range applied to any output in the high or low state	A port	-0.5	4.6		
vo		B port	-0.5	4.6	V	
I _{IK}	Input clamp current	V _I < 0		-50	mA	
I _{OK}	Output clamp current	V _O < 0		-50	mA	
I _O	Continuous output current		±50	mA		
	Continuous current through V _{CCA} or GND		±100	mA		
T _{stg}	Storage temperature range		-65	150	°C	

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL IMPEDANCE RATINGS

			UNIT
θ_{JA}	Package thermal impedance ⁽¹⁾	117	°C/W

(1) The package thermal impedance is calculated in accordance with JESD 51-7.



RECOMMENDED OPERATING CONDITIONS⁽¹⁾ Level Translator

			V _{CCA}	V _{CCB}	MIN	MAX	UNIT
V _{CCA}	Supply voltage				1.1	3.6	V
V _{CCB}	Supply voltage				1.1	3.6	V
		A-Port CMD and	1.1 V to 1.95 V	1.1 V to 1.95 V			
V _{IH}	High-level input voltage	DATA I/Os B-Port CMD and DATA I/Os	1.95 V to 3.6 V	1.95 V to 3.6 V	V _{CCI} - 0.2	V _{CCI}	V
		EN and CLKA	1.1 V to 3.6 V	1.1 V to 3.6 V	V _{CCI} x 0.65	V _{CCI}	
		A-Port CMD and	1.1 V to 1.95 V	1.1 V to 1.95 V			
V _{IL}	Low-level input voltage	DATA I/Os B-Port CMD and DATA I/Os	1.95 V to 3.6 V	1.95 V to 3.6 V	0	0.15	V
		EN and CLKA	1.1 V to 3.6 V	1.1 V to 3.6 V	0	V _{CCI} x 0.35	
V		Active state			0	V _{cco}	V
۷O	Oulput voltage	3-state			0	3.6	v
			1.1 V to 3.6 V			-100	μA
			1.1 V to 1.3 V			-0.5	mA
1	High lovel output our	ront (CLK foutput)	1.4 V to 1.6 V	11V to 26V		-1	
ЮН	High-level output cur	ieni (CER-i ouipui)	1.65 V to 1.95 V	1.1 V to 5.6 V		-2	
			2.3 V to 2.7 V			-4	
			3 V to 3.6 V			-8	
			1.1 V to 3.6 V			100	μA
			1.1 V to 1.3 V			0.5	
1	Low lovel output our	ont (CLK foutput)	1.4 V to 1.6 V	1.1 V to 3.6 V		1	mA
OL			1.65 V to 1.95 V			2	
			2.3 V to 2.7 V			4	
			3 V to 3.6 V			8	
				1.1 V to 3.6 V		-100	μA
				1.1 V to 1.3 V		-0.5	
1	High-level output our	rent (CLK output)	1 1 \/ to 3 6 \/	1.4 V to 1.6 V	-1		
ЮН			1.1 V 10 5.0 V	1.65 V to 1.95 V		-2	mA
				2.3 V to 2.7 V		-4	
				3 V to 3.6 V		-8	
				1.1 V to 3.6 V		100	μA
				1.1 V to 1.3 V		0.5	
	Low lovel output our	ront (CLK output)	11\/ to 36\/	1.4 V to 1.6 V		1	
OL			1.1 V 10 5.0 V	1.65 V to 1.95 V		2	mA
				2.3 V to 2.7 V		4	
				3 V to 3.6 V		8	
Δt/Δv	Input transition rise o	r fall rate				5	ns/V
T _A	Operating free-air ter	nperature			-40	85	°C

(1) All unused data inputs of the device must be held at V_{CCI} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



ELECTRICAL CHARACTERISTICS Level Translator

over recommended operating free-air temperature range (unless otherwise noted)

F	ARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	MIN	TYP ⁽¹⁾ MAX	UNIT
		I _{OH} = -100 μA	1.1 V to 3.6 V		V _{CCA} * 0.8		
		I _{OH} = -0.5 mA	1.1 V		0.8		
	A port	$I_{OH} = -1 \text{ mA}$	1.4 V		1.05		
	(CLK-f output)	$I_{OH} = -2 \text{ mA}$	1.65 V		1.2		
V _{OH}		$I_{OH} = -4 \text{ mA}$	2.3 V	1.1 V to 3.6 V	1.75		V
		I _{OH} = -8 mA	3 V		2.3		
	A port (DAT and CMD outputs)	I _{OH} = -20 μA	1.1 V to 3.6 V	-	$V_{CCA} \times 0.8$		
		I _{OL} = 100 μA	1.1 V to 3.6 V			V _{CCA} × 0.8	
		I _{OL} = 0.5 mA	1.1 V			0.35	V
	A port (CLK-f output)	I _{OL} = 1 mA	1.4 V	1.1 V to 3.6 V		0.35	
		I _{OL} = 2 mA	1.65 V 2.3 V			0.45	
		I _{OL} = 4 mA				0.55	
V _{OL}		I _{OL} = 8 mA	3 V			0.7	
		I _{OL} = 135 μA				0.4	
	A port	I _{OL} = 180 μA				0.4	
	(DAT and CMD	I _{OL} = 220 μA	1.1 V to 3.6 V			0.4	V
	outputs)	I _{OL} = 300 μA				0.4	1
		I _{OL} = 400 μA				0.55	
		I _{OH} = -100 μA		1.1 V to 3.6 V	$V_{CCA} \times 0.8$		
		I _{OH} = -0.5 mA		1.1 V	0.8		
	B port	$I_{OH} = -1 \text{ mA}$		1.4 V	1.05		
Vou	(CLK output)	$I_{OH} = -2 \text{ mA}$	1.1 V to 3.6 V	1.65 V	1.2		V
· 0H		$I_{OH} = -4 \text{ mA}$		2.3 V	1.75		
		I _{OH} = -8 mA		3 V	2.3		
	B port (DAT output)	I _{OH} = -20 μA		1.1 V to 3.6 V	$V_{CCA} \times 0.8$		

(1) All typical values are at $T_A = 25^{\circ}C$.



ELECTRICAL CHARACTERISTICS Level Translator (continued)

F	PARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	MIN TYP ⁽¹⁾ MAX	UNIT
		I _{OL} = 100 μA		1.1 V to 3.6 V	V _{CCA} × 0.8	
		I _{OL} = 0.5 mA		1.1 V	0.35	i i
	B port	I _{OL} = 1 mA	111/10261/	1.4 V	0.35	V
		I _{OL} = 2 mA	1.1 V 10 3.6 V	1.65 V	0.45	v
		I _{OL} = 4 mA		2.3 V	0.55	1
V _{OL}		I _{OL} = 8 mA		3 V	0.7	
		I _{OL} = 135 μA		1.1 V to 3.6 V	0.4	
		I _{OL} = 180 μA		1.4 V	0.4	
	B port (DAT output)	I _{OL} = 220 μA	1.1 V to 3.6 V	1.65 V	0.4	V
		I _{OL} = 300 μA		2.3 V	0.4	
		I _{OL} = 400 μA		3 V	0.55	i -
I _I	Control inputs	$V_I = V_{CCA}$ or GND		1.1 V to 3.6 V	±1	μA
I_{CCA}		$V_{I} = V_{CCI} \text{ or } GND, I_{O} = 0$	1.1 V to 3.6 V	1.1 V to 3.6 V	6	μA
I _{CCB}		$V_{I} = V_{CCI} \text{ or } GND, I_{O} = 0$	1.1 V to 3.6 V	1.1 V to 3.6 V	5	μA
C	A port				5.5 6.5	n F
Cio	B port				15 17.5	рг
~	Control inputs				3.5 4.5	~ 5
Ci	Clock input	$v_1 = v_{CCA}$ or GND			3 4	p r

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TIMING REQUIREMENTS

 $V_{CCA} = 1.2 V \pm 0.1 V$

over recommended operating free-air temperature range (unless otherwise noted)

			V _{ССВ} = ± 0.1	1.2 V V	V _{CCB} = ± 0.	: 1.5 V 1 V	V _{CCB} = ± 0.1	: 1.8 V 5 V	V _{CCB} = ± 0.2	2.5 V 2 V	V _{CCB} = ± 0.3	3.3 V 5 V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Commond	Push-pull driving		30		40		40		40		40	Mhoo
Doto roto	Command	Open-drain driving		0.9		1		1		1		1	ivibps
Dala Tale	Clock	Duch pull driving		30		40		50		60		60	MHz
	Data	Push-pull allving		30		40		40		40		40	Mbps
	Commond	Push-pull driving	33		25		25		25		25		ns
, Pulse	Command	Open-drain driving	1		1		1		1		1		μs
w duration	Clock	Duch pull driving	16.7		12.5		10		8.3		8.3		ns
	Data	Fush-puil driving	33		25		25		25		25		ns

TIMING REQUIREMENTS

 $V_{CCA} = 1.5 V \pm 0.1 V$

over recommended operating free-air temperature range (unless otherwise noted)

			V _{ССВ} = ± 0.1	1.2 V V	V _{ССВ} = ± 0.	= 1.5 V 1 V	V _{ССВ} = ± 0.1	: 1.8 V I5 V	V _{CCB} = ± 0.2	2.5 V 2 V	V _{CCB} = ± 0.3	3.3 V 8 V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Command	Push-pull driving		30		60		60		60		60	Mhoo
Doto roto	Command	Open-drain driving		1		1		1		1		1	wops
Dala Tale	Clock	Duch null driving		50		60		60		60		60	MHz
	Data	Push-puil anving		30		60		60		60		60	Mbps
	Command	Push-pull driving	33		17		17		17		17		ns
, Pulse	Commanu	Open-drain driving	1		1		1		1		1		μs
w duration	Clock	Duch null driving	10		8.3		8.3		8.3		8.3		ns
	Data	Fush-puil driving	33		17		17		17		17		ns

TIMING REQUIREMENTS $V_{CCA} = 1.8 \text{ V} \pm 0.15 \text{ V}$

			V _{CCB} = ± 0.1	1.2 V V	V _{CCB} = ± 0.	: 1.5 V 1 V	V _{ССВ} = ± 0.1	: 1.8 V 5 V	V _{CCB} = ± 0.2	2.5 V 2 V	V _{CCB} = ± 0.3	3.3 V V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Command	Push-pull driving		30		60		60		60		60	Mhoo
Data rata	Commanu	Open-drain driving		1		1		1		1		1	wipps
Data Tate	Clock	Duch null driving		50		60		60		60		60	MHz
	Data	Push-puil anving		30		60		60		60		60	Mbps
	Command	Push-pull driving	33		17		17		17		17		ns
, Pulse	Commanu	Open-drain driving	1		1		1		1		1		μs
^ι W duration	Clock	Duch null driving	10		8.3		8.3		8.3		8.3		ns
	Data	Push-puil ariving	33		17		17		17		17		ns



TIMING REQUIREMENTS

 $V_{CCA} = 2.5 V \pm 0.2 V$

over recommended operating free-air temperature range (unless otherwise noted)

			V _{ССВ} = ± 0.1	1.2 V V	V _{CCB} = ± 0.1	: 1.5 V 1 V	V _{ССВ} = ± 0.1	= 1.8 V I5 V	V _{CCB} = ± 0.2	2.5 V 2 V	V _{CCB} = ± 0.3	3.3 V 8 V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Command	Push-pull driving		30		60		60		60		60	Mhaa
Doto roto	Command	Open-drain driving		1		1		1		1		1	ivibps
Dala Tale	Clock	Duch pull driving		60		60		60		60		60	MHz
	Data	Push-pull allving		30		60		60		60		60	Mbps
	Command	Push-pull driving	33		17		17		17		17		ns
_ Pulse	Commanu	Open-drain driving	1		1		1		1		1		μs
w duration	Clock	Duch null driving	8.3		8.3		8.3		8.3		8.3		ns
	Data	Fush-puil driving	33		17		17		17		17		ns

TIMING REQUIREMENTS

 $V_{CCA} = 3.3 \text{ V} \pm 0.3 \text{ V}$

			V _{ССВ} = ± 0.1	1.2 V I V	V _{ССВ} = ± 0.	= 1.5 V 1 V	V _{ССВ} = ± 0.1	= 1.8 V 15 V	V _{ССВ} = ± 0.2	2.5 V 2 V	V _{ССВ} = ± 0.3	3.3 V V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Command	Push-pull driving		30		60		60		60		60	Mhaa
Doto roto	Command	Open-drain driving		0.9		1		1		1		1	Mbps
Dala Tale	Clock	Duch null driving		55		55		55		55		55	MHz
	Data	Push-puil anving		30		60		60		60		60	Mbps
	Command	Push-pull driving	33		17		17		17		17		ns
_ Pulse	Commanu	Open-drain driving	1		1		1		1		1		μs
w duration	Clock	Duch null driving	9		9		9		9		9		ns
	Data	Fush-puil driving	33		17		17		17		17		ns

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SWITCHING CHARACTERISTICS

 $V_{CCA} = 1.2 \text{ V} \pm 0.1 \text{ V}$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _C = 1. ± 0.	^{св} 2 V 1 V	V _C = 1. ± 0.	св 5 V 1 V	V _C = 1. ± 0.1	св 8 V I5 V	V _C = 2. ± 0.	св 5 V 2 V	V _C = 3. ± 0.	св 3 V 3 V	UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
			Push-pull driving		15.3		12.2		10.8		10.4		10.8	
	CMDA	CMDB	Open-drain driving (H-to-L)	4.1	16.6	3.7	12.6	3.4	11.5	3.3	10.6	3.2	10.3	
			Open-drain driving (L-to-H)	204	308	164	256	133	224	95	175	71	147	
			Push-pull driving		19.7		15.1		13.4		12		11.2	
t _{pd}	CMDB	CMDA	Open-drain driving (H-to-L)	4.7	19.4	3.8	12.4	3.4	10.5	3.1	9.2	2.9	9.4	ns
			Open-drain driving (L-to-H)	211	353	170	304	139	282	101	243	77	204	
	CLKA	CLKB	Push-pull driving		15.6		12.3		11.5		10.9		11.7	
	DATxA	DATxB	Duch pull driving		15.9		12.6		11.2		10.7		11.1	
	DATxB	DATxA	Push-puil anving		18.2		14.3		12.8		11.5		10.6	
	CLKA	CLK-f	Push-pull driving		37.9		30.7		26.8		24.7		24.2	
	EN	B-port	Push-pull driving		1		1		1		1		1	110
Len	EN	A-port	Push-pull driving		1		1		1		1		1	μs
	EN	B-port	Push-pull driving		68		55		46		40		38	
ldis	EN	A-port	Push-pull driving		62		56		48		40		37	ns
	CMDA	ria a tima a	Push-pull driving	1.7	14.1	1.5	13	1.5	12.7	1.6	12.2	1.9	11.9	
	CIVIDA	nse ume	Open-drain driving	170	260	128	205	96	171	57	120	32	91	
٩rA	CLK-f	rise time	Buch pull driving	0.6	10.6	0.6	10.9	0.6	12	0.6	12.3	0.6	12.7	ns
	DATxA	rise time	Push-puil anving	1.7	13.7	1.5	12.6	1.5	12	1.6	11.6	1.9	11.5	
	CMDD	riaa timaa	Push-pull driving	1.9	12.4	2.3	9.2	1.9	7.3	1.8	6.7	1.7	3.9	
	CIVIDB	nse ume	Open-drain driving	175	300	145	261	118	245	86	214	66	181	
t _{rB}	CLKB	rise time	Duch null driving	1	7.7	0.8	7.1	0.8	6.2	1.7	4.8	1.7	4.3	ns
	DATxB	rise time	Push-puli anving	2.9	11.8	2.3	8.9	1.9	7.4	0.9	4.7	0.4	6.8	
	CMDA	foll time	Push-pull driving	1	8	1	5.4	1	4.5	1	3.9	0.8	4	
	CIVIDA		Open-drain driving	2.3	8.3	1.9	4.9	1.7	4.4	1.6	3.9	1.6	3.7	20
٩fA	CLK-f	fall time	Duch pull driving	1	5.8	1	4.6	1	4.1	1	3.8	1	4	115
	DATxA	fall time	Push-pull anving	1.8	8	1.3	5.4	1	4.5	1	3.9	1	3.8	
	CMDP	foll time	Push-pull driving	2.1	7.9	1.8	5.2	1.7	4.6	1.6	4.5	1.5	4.3	
	CIVIDB		Open-drain driving	1.9	8.3	1.5	5.9	1.3	5.1	1.1	4.3	1	4.2	20
lfΒ	CLKB	fall time	Duch pull driving	2	7.1	1.8	5.4	1.8	4.5	1.7	4	1.6	3.9	115
	DATxB	s fall time	Push-puli unving	2.1	8.5	1.1	6.4	0.9	5	1	3.9	1.1	4.8	
t _{SK(O)}	Channel- sł	-to-channel kew	Push-pull driving		1		1		1		1		1	ns
	0.	mond	Push-pull driving		30		40		40		40		40	Mbere
New data anti-	Corr	imand	Open-drain driving		0.9		1		1		1		1	sqaw
wax data rate	C	lock	Duch null definite e		30		40		50		60		60	MHz
	D	ata	Fush-puil driving		30		40		40		40		40	Mbps



SWITCHING CHARACTERISTICS

 $V_{CCA} = 1.5 V \pm 0.1 V$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _C = 1. ± 0.	св 2 V 1 V	V _C = 1. ± 0.	св 5 V 1 V	V _C = 1. ± 0.1	св 8 V 15 V	V _C = 2. ± 0.	^{св} 5 V 2 V	V _C = 3. ± 0.	св 3 V 3 V	UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
			Push-pull driving		12		8.6		6.9		6.1		6	
	CMDA	CMDB	Open-drain driving (H-to-L)	3.7	12.8	3.2	8.7	2.9	7.6	2.7	6.6	2.7	6.5	
			Open-drain driving (L-to-H)	192	297	191	295	157	252	112	180	83	138	
			Push-pull driving		15.2		9.8		8		6.8		6.3	
t _{pd}	CMDB	CMDA	Open-drain driving (H-to-L)	3.7	20.4	2.9	11.8	2.5	9.4	2.2	7.3	2.1	6.6	ns
			Open-drain driving (L-to-H)	199	337	196	316	162	282	117	214	87	177	
	CLKA	CLKB	Push-pull driving		12.3		8.7		7.7		6.1		6.2	
	DATxA	DATxB	Duch null driving		12.5		8.9		7.2		6.2		6.1	
	DATxB	DATxA	Pusn-pull ariving		13.9		9.2		7.6		6.5		6.1	
	CLKA	CLK-f	Push-pull driving		29		20		16		13		12	
	EN	B-port	Push-pull driving		1		1		1		1		1	
t _{en}	EN	A-port	Push-pull driving		1		1		1		1		1	μs
	EN	B-port	Push-pull driving		57		53		46		39		37	
t _{dis}	EN	A-port	Push-pull driving		58		54		46		38		35	ns
	CMDA	ria a tima a	Push-pull driving	1.6	10.5	0.4	9.5	0.2	8.9	0.4	8.3	1	7.9	
	CIVIDA	nse ume	Open-drain driving	166	254	157	247	121	203	74	127	44	85	
٩rA	CLK-f	rise time	Duch pull driving	0.5	5.5	0.5	5.5	0.5	6.2	0.5	7	0.5	7.2	ns
	DATxA	rise time	Push-puli anving	2	10.3	0.7	9.4	0.5	8.9	0.6	8.4	0.7	8.3	
	CMDB	rico timo	Push-pull driving	1.9	11.2	2	8	1.9	6.5	0.5	5.6	0.5	3.1	
	CIVIDB	nse ume	Open-drain driving	157	273	163	264	135	253	96	196	71	165	20
ι _{rB}	CLKB	rise time	Duch pull driving	1.3	7.5	0.6	6.7	0.4	5.9	1.5	4.9	1.9	4.3	ns
	DATxB	rise time	Push-pull anving	2.2	10.9	2	8.4	1.7	6.9	0.8	5	0.6	4	
	CMDA	foll time	Push-pull driving	1.5	5.5	1.3	3.8	0.9	2.9	0.8	2.3	0.8	2.3	
+	CIVIDA		Open-drain driving	2.3	8	2	4.8	1.8	4.2	1.7	3.7	1.6	3.5	00
ЧfА	CLK-f	fall time	Push-pull driving	0.4	3.9	0.4	3.7	0.4	4	0.4	3.7	0.4	6.8	115
	DATxA	fall time		0.8	6	0.6	4.8	0.1	4.1	0.1	3.8	0.1	3.8	
	CMDB	foll time	Push-pull driving	1	11.6	1.5	7.1	1.5	5.8	1.4	5.4	1.6	3.6	
+	CIVIDB		Open-drain driving	1.7	5.2	1.5	3.8	1.2	3	1	2.3	0.9	2.3	00
٩fB	CLKB	fall time	Push pull driving	1.1	10.8	1	8.8	1.8	6	1.7	4.1	1.6	3.9	115
	DATxE	s fall time		1.1	13.3	1.2	7.7	1.2	6.5	2.3	4.3	2.5	4.2	
t _{SK(O)}	Channel- sl	-to-channel kew	Push-pull driving		1		1		1		1		1	ns
	0	mond	Push-pull driving		30		60		60		60		60	Mhaa
Max data rata	Con	manu	Open-drain driving		1		1		1		1		1	IVIDPS
	С	lock			50		60		60		60		60	MHz
	D	ata	r usii-puli uliviliy		30		60		60		60		60	Mbps

SCES697C - AUGUST 2009 - REVISED JANUARY 2010

SWITCHING CHARACTERISTICS $V_{CCA} = 1.8 V \pm 0.15 V$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST	V _C = 1. ± 0.	св 2 V 1 V	V _C = 1. ± 0.	св 5 V 1 V	V _C = 1. ± 0.1	св 8 V I5 V	V _C = 2. ± 0.	св 5 V 2 V	V _C = 3. ± 0.	св 3 V 3 V	UNIT
	(- <i>)</i>	(/		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
			Push-pull driving		11.3		7.3		5.7		4.6		4.4	
	CMDA	CMDB	Open-drain driving (H-to-L)	3.4	11.8	2.9	7.6	2.7	6.5	2.5	5.5	2.4	5.1	
			Open-drain driving (L-to-H)	179	286	183	288	168	286	121	201	89	151	
			Push-pull driving		13.2		8.3		6.5		5.2		4.8	
t _{pd}	CMDB	CMDA	Open-drain driving (H-to-L)	3.5	19.7	2.8	11.1	2.4	8.6	2.1	6.4	2	5.7	ns
			Open-drain driving (L-to-H)	186	323	190	304	173	303	125	215	93	166	
	CLKA	CLKB	Push-pull driving		11.6		7.7		6.2		4.7		4.5	
	DATxA	DATxB	Duch null driving		11.7		7.5		5.8		4.7		4.4	
	DATxB	DATxA	Pusn-pull ariving		12.1		7.9		6.3		5		4.6	
	CLKA	CLK-f	Push-pull driving		25.1		16.5		12		8.9		7.9	
	EN	B-port	Push-pull driving		1		1		1		1		1	
t _{en}	EN	A-port	Push-pull driving		1		1		1		1		1	μs
	EN	B-port	Push-pull driving		39		37		37		35		35	
t _{dis}	EN	A-port	Push-pull driving		49		47		47		38		35	ns
	OMDA		Push-pull driving	1.8	8.4	1.2	6.8	1.1	5.9	1.1	5.9	1.6	5.8	
	CIVIDA	rise time	Open-drain driving	154	246	155	262	135	238	85	150	52	99	
t _{rA}	CLK-f	rise time	Duch cull debrie e	0.4	4	0.4	4.3	0.4	4.7	0.4	4.5	0.4	4.1	ns
	DATxA	rise time	Push-pull anving	1.9	8.6	1.2	7.1	0.9	6.8	1	6.3	1.3	6.1	
	CMDD	ria a tima a	Push-pull driving	1.8	10.2	2	7.7	1.7	6.5	1	5.2	1.7	3.1	
	CIVIDB	nse ume	Open-drain driving	137	251	148	245	141	251	100	184	73	142	
ι _{rB}	CLKB	rise time	Duch null driving	1.5	7.3	0.7	6.6	0.4	5.9	1.5	4.9	1.9	4.3	ns
	DATxB	rise time	Push-pull anving	2.3	10.3	1.8	8	1.5	6.8	0.9	5.2	0.2	5	
		fall time	Push-pull driving	0.6	4.5	0.4	3.8	0.2	3.3	0.2	2.9	0.2	3.1	
	CIVIDA		Open-drain driving	2.3	7.9	2	4.8	1.8	4.2	1.7	3.7	1.6	3.5	
^L fA	CLK-f	fall time	Duch null driving	0.1	2	0.2	2.2	0.7	1.6	0.7	1.5	0.1	3	115
	DATxA	fall time	Push-pull driving	1	4.3	0.8	3.6	1	2.7	0.1	2.7	0.2	2.6	
	CMDD	fall time	Push-pull driving	1	10.3	1.4	6.8	1.8	5.4	1.6	5	1.6	3.6	
	CIVIDB	all time	Open-drain driving	1.4	4	1.3	3	1.2	2.6	0.9	1.9	0.8	1.8	20
^L fB	CLKB	fall time	Duch null driving	1.1	10.8	1	10.3	1.4	6.3	1.8	4.2	1.7	4	115
	DATxE	3 fall time	Push-pull anving	1	11.8	15	7	1.2	6.3	1.6	4.9	0.8	3.6	
t _{SK(O)}	Channel- sl	-to-channel kew	Push-pull driving		1		1		1		1		1	ns
	0		Push-pull driving		30		60		60		60		60	N dia an
May data anti	Con	imand	Open-drain driving		1		1		1		1		1	ivipps
wax uata rate	С	lock	Duch null driving		50		60		60		60		60	MHz
	D	lata	Fush-puil ariving		30		60		60		60		60	Mbps



SWITCHING CHARACTERISTICS V_{CCA} = 2.5 V ± 0.2 V

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _C = 1. ± 0.	^{св} 2 V 1 V	V _C = 1. ± 0.	св 5 V 1 V	V _C = 1. ± 0.1	св 8 V 15 V	V _C = 2. ± 0.	^{св} 5 V 2 V	V _C = 3. ± 0.	св 3 V 3 V	UNIT
	(-)	(,		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
			Push-pull driving		10.6		6.5		4.9		3.7		3.3	
	CMDA	CMDB	Open-drain driving (H-to-L)	3.2	10.9	2.7	6.7	2.4	5.5	2.2	4.4	2.1	4.1	
			Open-drain driving (L-to-H)	156	253	162	258	149	261	126	249	98	190	
			Push-pull driving		12.5		7.4		5.6		4.1		3.6	
t _{pd}	CMDB	CMDA	Open-drain driving (H-to-L)	3.5	19.2	2.7	10.5	2.3	7.9	2	5.7	1.9	4.8	ns
			Open-drain driving (L-to-H)	163	295	169	273	158	274	131	261	99	202	
	CLKA	CLKB	Push-pull driving		10.8		6.8		5.4		3.7		3.4	
	DATxA	DATxB	Duch cull debrie e		10.9		6.7		5		3.7		3.3	
	DATxB	DATxA	Pusn-pull driving		11.5		7.1		5.4		3.9		3.5	
	CLKA	CLK-f	Push-pull driving		23.7		14.9		10.2		6.8		5.7	
	EN	B-port	Push-pull driving		1		1		1		1		1	
t _{en}	EN	A-port	Push-pull driving		1		1		1		1		1	μs
	EN	B-port	Push-pull driving		48		45		45		38		36	
t _{dis}	EN	A-port	Push-pull driving		45		38		38		38		35	ns
	01454		Push-pull driving	1.9	4.7	1.7	4.4	1.7	3.8	1.9	3.2	2.3	3.3	
	CMDA	rise time	Open-drain driving	135	216	136	237	121	228	96	201	62	141	
t _{rA}	CLK-f	rise time	D	0.8	1.6	0.3	1.9	0.6	1.8	0.7	1.5	0.7	1.3	ns
	DATxA	rise time	Pusn-pull driving	1.9	6.1	1.8	4.5	1.7	4.1	1.9	4	1.8	4.2	
	01100		Push-pull driving	1.7	10.8	2.9	7.6	1.8	6.6	1.5	5.2	1.5	3.8	
	CMDB	rise time	Open-drain driving	102	205	116	197	112	207	101	214	76	165	
t _{rB}	CLKB	rise time	D	1.6	7.3	0.5	6.8	0.4	5.8	1.6	5	1.7	4.4	ns
	DATxB	rise time	Pusn-pull driving	2.2	10.3	1.9	7.9	1.8	6.6	1.4	5.3	0.9	4.4	
	0145.4	6 H C	Push-pull driving	0.4	2.4	0.4	1.6	0.4	1.5	0.5	1.5	0.3	1.4	
	CMDA	tall time	Open-drain driving	2.2	7.6	1.9	4.8	1.8	4.2	1.7	3.7	1.6	3.5	
t _{fA}	CLK-f	fall time	Duch cull debrie e	0.3	2.2	0.3	2.7	0.3	2.6	0.3	2.4	0.3	2.8	ns
	DATxA	fall time	Pusn-pull ariving	0.4	4	0.4	3.6	0.4	3.2	0.5	2.9	0.3	2.6	
			Push-pull driving	1	13.4	1.8	7.2	1.7	6.3	1.6	5.6	1.6	3.7	
	CMDB	fall time	Open-drain driving	1	2.3	1	1.7	1	1.7	1	1.6	0.8	1.4	
t _{fB}	CLKB	fall time		1.1	12.7	1	11.3	0.9	8.7	1.8	4.5	1.7	4.1	ns
	DATxE	s fall time	Push-pull driving	1	16	0.7	9	08	7	0.8	4.9	0.2	4	
t _{SK(O)}	Channel- sl	-to-channel kew	Push-pull driving		1		1		1		1		1	ns
	-		Push-pull driving		30		60		60		60		60	• •
	Corr	nmand	Open-drain driving		1		1		1		1		1	Mbps
Max data rate	С	lock			50		60		60		60		60	MHz
	D	ata	Pusn-pull driving		30		60		60		60		60	Mbps

SCES697C - AUGUST 2009 - REVISED JANUARY 2010

SWITCHING CHARACTERISTICS

 $V_{CCA} = 3.3 \text{ V} \pm 0.3 \text{ V}$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _C = 1. ± 0.	св 2 V 1 V	V _C = 1. ± 0.	св 5 V 1 V	V _C = 1. ± 0.1	св 8 V I5 V	V _C = 2. ± 0.	св 5 V 2 V	V _C = 3. ± 0.	св 3 V 3 V	UNIT
	. ,	. ,		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
			Push-pull driving		12.5		7.2		5.3		3.8		3.2	
	CMDA	CMDB	Open-drain driving (H-to-L)	3.2	10.6	2.7	6.4	2.4	5.2	2.1	4.1	2	3.7	
			Open-drain driving (L-to-H)	136	212	141	235	129	235	112	233	101	201	
			Push-pull driving		10.7		6.6		5.1		3.4		3	
t _{pd}	CMDB	CMDA	Open-drain driving (H-to-L)	4.3	16.4	3.3	8.7	2.8	6.6	2.4	4.6	2.2	3.6	ns
			Open-drain driving (L-to-H)	142	273	148	246	139	248	122	248	105	212	
	CLKA	CLKB	Push-pull driving		10.8		6.5		4.8		3.5		3.1	
	DATxA	DATxB	Push pull driving		11.5		6.9		5.1		3.7		3.2	
	DATxB	DATxA	r usii-puli unvilig		23.6		14.4		9.6		6.2		5.1	
	CLKA	CLK-f	Push-pull driving		17.1		9.1		6.8		4.8		4.2	
	EN	B-port	Push-pull driving		1		1		1		1		1	
Len	EN	A-port	Push-pull driving		1		1		1		1		1	μs
	EN	B-port	Push-pull driving		38		34		34		34		34	
ldis	EN	A-port	Push-pull driving		45		37		36		36		35	ns
	CMDA	riaa timaa	Push-pull driving	0.7	5.6	0.7	5	0.7	4.2	0.8	4.1	1	4.2	
	CIVIDA	nse ume	Open-drain driving	117	178	118	213	104	206	85	194	74	155	
٩rA	CLK-f	rise time	Duch null driving	0.7	1.5	0.5	1.7	0.7	1.5	0.7	1.4	0.7	1.4	ns
	DATxA	rise time	Push-puil anving	0.9	5	1.1	3.9	1.3	3.4	1.4	3.3	1.1	3	
	CMDD	riaa timaa	Push-pull driving	1.7	10.8	2.3	7.4	2.2	6.4	2	5	1.9	4	
	CIVIDB	nse ume	Open-drain driving	69	167	84	156	83	167	79	185	79	166	
t _{rB}	CLKB	rise time	Duch null driving	1	7.7	0.3	7.1	0.5	5.9	1.6	5.1	1.9	4.4	ns
	DATxB	rise time	Push-pull anving	2.1	10.5	2	7.9	2	6.6	1.8	5.3	1	14	
		fall time	Push-pull driving	0.3	2.8	0.4	2.4	0.4	2	0.4	2	1	2.3	
	CIVIDA	ian ume	Open-drain driving	2	7.6	1.8	5	1.7	4.4	1.6	3.9	1.6	3.7	
lfA	CLK-f	fall time	Duch null driving	0.6	1.3	0.6	1.3	0.6	1.3	0.6	1.3	0.6	1.3	ns
	DATxA	fall time	Push-pull anving	0.3	2.7	0.4	2.3	0.4	1.4	0.4	1.8	0.5	1.7	
	OMDD	f = f = = =	Push-pull driving	1	13.3	0.7	7.9	0.9	6.2	0.8	6.3	1	5	
	CINDB	tall time	Open-drain driving	0.7	1.5	0.7	1.4	0.8	1.4	0.9	1.3	0.9	1.3	
ι _{fB}	CLKB	fall time	Durah and debring	1	15.5	1	9.1	0.9	7.8	0.9	5.1	0.9	4.3	ns
	DATxE	s fall time	Pusn-pull driving	1	15	0.9	6.8	0.9	6.8	0.8	6.9	0.8	5	
t _{SK(O)}	Channel- sl	-to-channel kew	Push-pull driving		1		1		1		1		1	ns
	_		Push-pull driving		30		60		60		60		60	
	Con	nmand	Open-drain driving		0.9		1		1		1		1	Mbps
Max data rate	С	lock	D		55		55		55		55		55	MHz
	D	ata	Pusn-pull ariving		30		60		60		60		60	Mbps



TXS0206

OPERATING CHARACTERISTICS

 $T_A = 25^{\circ}C, V_{CCA} = 1.2 V$

		D	TEST			V _{CCB}	ТҮР			
	PARAMET	:K	CONDITIONS	1.2 V	1.5 V	1.8 V	2.5 V	3 V	3.3 V	UNIT
	A-port input,	CLK Enabled		15	15	14.9	14.9	15	15	
	output	DATA Enabled		6.3	6.4	6.5	6.5	6.5	6.5	
c (1)	B-port input, A-port output	DATA Enabled	$C_L = 0,$	12.5	12.3	12.3	12.1	12	11.9	- 5
C _{pdA} ()	A-port input,	CLK Disabled	$t_r = t_f = 1 \text{ ns}$	0.2	0.2	0.2	0.3	0.3	0.3	рғ
	output	DATA Disabled		1.2	1.2	1.2	1.2	1.2	1.2	
	B-port input, A-port output	DATA Disabled		0.2	0.2	0.2	0.3	0.3	0.3	
	A-port input, B-port output	DATA Enabled		26.2	27.3	28.2	29.7	30	31.2	
	B-port input,	CLK Enabled		25.7	25.6	25.6	26.4	27	28.1	
C (1)	output	DATA Enabled	$C_{L} = 0,$	13.7	12.2	11.4	12	12.5	12.9	۶E
C _{pdB} (A-port input, B-port output	DATA Disabled	$t_r = t_f = 1 \text{ ns}$	0.6	0.5	0.5	0.5	0.5	0.6	рг
	B-port input,	CLK Disabled		0.6	0.5	0.5	0.5	0.5	0.6	
	output	DATA Disabled		1.2	1.2	1.2	1	1	0.9	

(1) Power dissipation capacitance per transceiver

OPERATING CHARACTERISTICS

 $T_A = 25^{\circ}C, V_{CCA} = 1.5 V$

		-0	TEST			V _{CCB}	ТҮР			
	PARAMEI	=R	CONDITIONS	1.2 V	1.5 V	1.8 V	2.5 V	3 V	3.3 V	UNIT
	A-port input,	CLK Enabled		15	15	15	14.9	14.9	14.9	
	output	DATA Enabled		6.4	6.3	6.2	6	6	6	
C (1)	B-port input, A-port output	DATA Enabled	$C_L = 0,$	13.2	12.3	12.2	12	12	11.9	
C _{pdA} ()	A-port input,	CLK Disabled	$t_r = 10 \text{ MHz},$ $t_r = t_f = 1 \text{ ns}$	0.1	0.1	0.1	0.1	0.1	0.1	рг
	output	DATA Disabled		1.2	1.2	1.2	1.2	1.2	1.2	
	B-port input, A-port output	DATA Disabled		0.1	0.1	0.1	0.1	0.1	0.1	

(1) Power dissipation capacitance per transceiver

OPERATING CHARACTERISTICS (continued)

 $T_A = 25^{\circ}C, V_{CCA} = 1.5 V$

	PARAMETER		TEST	V _{CCB} TYP								
	PARAIVIET	EK .	CONDITIONS	1.2 V	1.5 V	1.8 V	2.5 V	3 V	3.3 V	UNIT		
C _{pdB} ⁽¹⁾	A-port input, B-port output	DATA Enabled		25.8	26.3	27.3	29.2	29.2	30.6	_		
	B-port input, A-port output	CLK Enabled		25.8	25.6	25.6	26.2	26.2	27.2			
		DATA Enabled	$C_{L} = 0,$ f = 10 MHz, $t_{r} = t_{f} = 1 \text{ ns}$	13.7	12.3	11.4	12	12	12.8	~ F		
	A-port input, B-port output	DATA Disabled		0.1	0.1	0.1	0.1	0.1	0.1	рг		
	B-port input, A-port output	CLK Disabled		0.1	0.1	0.1	0.1	0.1	0.1	-		
		DATA Disabled		1.2	1.2	1.1	1	1	0.9			

OPERATING CHARACTERISTICS

 $T_A = 25^{\circ}C, V_{CCA} = 1.8 V$

	PARAMETER	TEST	V _{CCB} TYP							
	PARAMEI	=R	CONDITIONS	1.2 V	1.5 V	1.8 V	2.5 V	3 V	3.3 V	UNIT
	A-port input,	CLK Enabled		15.2	15.1	15.1	15	15	15	
	output	DATA Enabled		6.7	6.2	5.8	5.4	5.4	5.3	
C _{pdA} ⁽¹⁾	B-port input, A-port output	DATA Enabled	$C_L = 0,$	13.9	13.1	12.4	12.1	12	11.9	
	A-port input,	CLK Disabled	$t_r = t_f = 1 \text{ ns}$	0.1	0.1	0.1	0.1	0.1	0.1	рг
	B-port output	DATA Disabled	-	1.3	1.3	1.3	1.3	1.3	1.3	
	B-port input, A-port output	DATA Disabled		0.1	0.1	0.1	0.1	0.1	0.1	
	A-port input, B-port output	DATA Enabled		25.9	26.1	26.7	28.8	28.8	30.3	- pF
	B-port input,	CLK Enabled		25.8	25.6	25.6	26.2	26.2	27	
C (1)	output	DATA Enabled	$C_{L} = 0,$	13.6	12.2	11.5	12.1	12.1	12.9	
C _{pdB} ("	A-port input, B-port output	DATA Disabled	$t_r = t_f = 1 \text{ ns}$	0.2	0.1	0.1	0.1	0.1	0.1	
	B-port input,	CLK Disabled		0.2	0.1	0.1	0.1	0.1	0.1	
	output	DATA Disabled		1.2	1.2	1.1	1	1	0.8	

(1) Power dissipation capacitance per transceiver

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TXS0206

OPERATING CHARACTERISTICS

 $T_A = 25^{\circ}C, V_{CCA} = 2.5 V$

	PARAMETER		TEST	V _{CCB} TYP								
	PARAMET	EK .	CONDITIONS	1.2 V	1.5 V	1.8 V	2.5 V	3 V	3.3 V	UNIT		
	A-port input,	CLK Enabled		16.2	16	15.9	15.8	15.8	15.7	-		
	output	DATA Enabled		7.3	6.5	5.9	5.5	5.4	5.3			
C _{pdA} ⁽¹⁾	B-port input, A-port output	DATA Enabled	$C_L = 0,$	15.3	14.6	14	13	12.8	12.5			
	A-port input,	CLK Disabled	$t_r = t_f = 1 \text{ ns}$	0.1	0.1	0.1	0.1	0.1	0.1	рг		
	output	DATA Disabled		1.3	1.3	1.3	1.3	1.3	1.3			
	B-port input, A-port output	DATA Disabled		0.1	0.1	0.1	0.1	0.1	0.1			
	A-port input, B-port output	DATA Enabled		25.6	25.8	26.2	27.6	29	29.5			
	B-port input,	CLK Enabled		25.9	25.7	25.7	26.2	26.5	26.9			
C = ⁽¹⁾	output	DATA Enabled	C _L = 0, f = 10 MHz	13.6	12.2	11.5	12.3	12.7	13.2			
C _{pdB} (1)	A-port input, B-port output	DATA Disabled	$t_r = t_f = 1 \text{ ns}$	0.3	0.1	0.1	0.1	0.1	0.1	pr		
	B-port input,	CLK Disabled		0.3	0.1	0.1	0.1	0.1	0.1			
	output	DATA Disabled		1.2	1.2	1.1	1	0.9	0.8			

(1) Power dissipation capacitance per transceiver

OPERATING CHARACTERISTICS

 $T_A = 25^{\circ}C, V_{CCA} = 3.3 V$

		- 0	TEST	V _{CCB} TYP							
	PARAMEI	=R	CONDITIONS	1.2 V	1.5 V	1.8 V	2.5 V	3 V	3.3 V	UNIT	
	A-port input, B-port output	CLK Enabled		18.3	17.7	17.5	17.3	17.2	17.1		
		DATA Enabled		8.1	7	6.2	5.7	5.6	5.6		
	B-port input, A-port output	DATA Enabled	$C_L = 0,$	17	16.1	15.6	14.8	14.4	14	~ F	
C _{pdA} ()	A-port input, B-port output	CLK Disabled	t = 10 MHZ, $t_r = t_f = 1 \text{ ns}$	0.1	0.1	0.1	0.1	0.1	0.1	рг	
		DATA Disabled		1.3	1.3	1.3	1.3	1.3	1.3		
	B-port input, A-port output	DATA Disabled		0.1	0.1	0.1	0.1	0.1	0.1		

(1) Power dissipation capacitance per transceiver

OPERATING CHARACTERISTICS (continued)

 $T_A = 25^{\circ}C, V_{CCA} = 3.3 V$

	PARAMETER	TEST	V _{CCB} TYP								
	FARAINEI	-R	CONDITIONS	1.2 V	1.5 V	1.8 V	2.5 V	3 V	3.3 V	UNIT	
C _{pdB} ⁽¹⁾	A-port input, B-port output	DATA Enabled		25.2	25.6	26	27.1	28	28.5		
	B-port input, A-port output	CLK Enabled		26	25.8	25.8	26.3	26.8	27		
		DATA Enabled	$C_{L} = 0,$ f = 10 MHz, $t_{r} = t_{f} = 1 \text{ ns}$	13.7	12.1	11.4	12.2	12.7	13.2	~	
	A-port input, B-port output	DATA Disabled		0.3	0.1	0.1	0.1	0.1	0.1	рг	
	B-port input, A-port output	CLK Disabled		0.3	0.1	0.1	0.1	0.1	0.1		
		DATA Disabled		1.2	1.2	1.1	1	0.9	0.8		



Figure 7. Typical ASIP EMI Filter Frequency Response



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PARAMETER MEASUREMENT INFORMATION



- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, dv/dt ≥ 1 V/ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- D. The outputs are measured one at a time, wit
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. V_{CCI} is the V_{CC} associated with the input port.
- I. V_{CCO} is the V_{CC} associated with the output port.
- J. All parameters and waveforms are not applicable to all devices.



PARAMETER MEASUREMENT INFORMATION (continued)

Figure 8. Load Circuit and Voltage Waveforms



APPLICATION INFORMATION

The TXS0206 has integrated pullup resistors on the data and command ports and their values dynamically change. When the port is in a low signal state, there is a nominal pullup resistor value of 40 k Ω , and power consumption is minimized. When the port is in a high signal state, the nominal pullup resistor value changes to 4 k Ω , and simultaneous switching performance is improved as a result. The threshold at which the resistance changes is approximately V_{CCx}/2.

When using the TXS0206 device with MMCs, SD, and Memory StickTM to ensure that a valid receiver input voltage high (V_{IH}) is achieved, the value of any pulldown resistors (external or internal to a memory card) must not be smaller than a 10-k Ω value. The impact of adding too heavy (i.e., <10-k Ω value) a pulldown resistor to the data and command lines of the TXS0206 device and the resulting 4-k Ω pullup / 10-k Ω pulldown voltage divider network has a direct impact on the V_{IH} of the signal being sent into the memory card and its associated logic.

The resulting V_{IH} voltage for the 10-k Ω pulldown resistor value would be:

 $V_{CC} \times 10 \text{ k}\Omega / (10 \text{ k}\Omega + 4 \text{ k}\Omega) = 0.714 \times V_{CC}$

This is marginally above a valid input high voltage for a 1.8-V signal (i.e., $0.65 \times V_{CC}$).

The resulting V_{IH} voltage for 20-k Ω pulldown resistor value would be: V_{CC} × 20 k Ω / (20 k Ω + 4 k Ω) = 0.833 × V_{CC}

Which is above the valid input high voltage for a 1.8-V signal of 0.65 \times V_{CC}.



10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TXS0206YFPR	ACTIVE	DSBGA	YFP	20	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(3T2, 3TR)	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TXS0206YFPR	DSBGA	YFP	20	3000	180.0	8.4	1.66	2.06	0.56	4.0	8.0	Q1



PACKAGE MATERIALS INFORMATION

19-Jun-2024



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TXS0206YFPR	DSBGA	YFP	20	3000	182.0	182.0	20.0

YFP0020



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.



YFP0020

EXAMPLE BOARD LAYOUT

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



YFP0020

EXAMPLE STENCIL DESIGN

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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